

Substitute for form 1449A/PTO				Complete if Known		
INFORMATION DISCLOSURE				Application Number	10/685,380	
				Filing Date	October 16, 2003	
STATEMENT BY APPLICANT				First Named Inventor	Shinji MAEKAWA	
(use as many sheets as necessary)				Art Unit	2818	
				Examiner Name	David Goodwin	
Sheet	1	of	ı	Attorney Docket Number	740756-2660	

			U.S. PATENT DOCUMENT	rs	
izaminer nitials	Cite No. '	U.S. Patent Document  Number - Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYŸŸ	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
06	·····	US-4,659,422	04/21/1987	Sakurai	
ì		US-6,322,625 B2	11/27/2001	Im	
		US-6,475,839 B2	11/05/2002	Zhang et al.	
		US-6,548,370 B1	04/15/2003	Kasahara et al.	
		US-6,599,788 B1	07/29/2003	Kawasaki et al.	
DG		US-6,730,550 B1	05/04/2004	Yamazaki et al.	
	·				

		F	OREIGN PATENT D	OCUMENTS		
Examiner Initials	Cite No.	Foreign Patent Document  Kind Code <sup>3</sup> Country Code <sup>3</sup> Number <sup>4</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Application of Cited Document	Pages, Cohumns, Lines, Where Relevant Passages or Relevant Figures Appear	J.
	+					
	<del> </del>					
					LL	
		OTHER PRIOR	ART – NON PATENT I	ATERATURE DOCUMENTS		
Examiner Initials	Cite No. 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.)., date, page(s), volume-issue number(s), publisher, city and/or country where published.				
76		Kazuhiro SHIMIZU et al., "High-Mobility Poly-Si Thin-Film Transistors Fabricated by a Novel Excimer Laser Crystallization Method", IEEE TRANSACTIONS ON ELECTRON DEVICES., Vol. 40, No. 1, 1993, pp. 112-117.				

					/
Examiner	1) 11 = 1/1	1,00	Date	11/2/	XP
Signature	I IMAN AN COURT	UV CH	Considered	111/201	01

<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>&</sup>lt;sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at <a href="https://www.uspto.gov">www.uspto.gov</a> or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the scrial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

<sup>&</sup>lt;sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.